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November 2013

# FQPF9P25

# P-Channel QFET® MOSFET

-250 V, -6 A, 620 mΩ

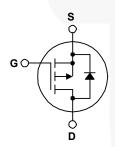
# **Description**

This P-Channel enhancement mode power MOSFET is  $\bullet$  -6 A, -250 V,  $R_{DS(on)}$  = 620 m $\Omega$  (Max.) @  $V_{GS}$  = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance • Low Crss (Typ. 27 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications.

# **Features**

- $I_{D} = -3 A$
- Low Gate Charge (Typ. 29 nC)





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQPF9P25	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		-250	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		-6.0	А	
	- Continuous (T <sub>C</sub> = 100°C)		-3.9	Α	
I <sub>DM</sub>	Drain Current - Pulsed	Note 1)	-24	А	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	Note 2)	650	mJ	
I <sub>AR</sub>	Avalanche Current	Note 1)	-6.0	А	
E <sub>AR</sub>	Repetitive Avalanche Energy	Note 1)	5.0	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-5.5	V/ns	
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		50	W	
	- Derate above 25°C		0.4	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C	

# **Thermal Characteristics**

Symbol	Parameter	FQPF9P25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF9P25	FQPF9P25	TO-220F	Tube	N/A	N/A	50 units

# **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Uni
Off Cha	aracteristics					
BV <sub>DSS</sub>	Orain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}, I_D = -250 \text{ μA}$		-250			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, Referenced to 25°C		-0.2	1	V/°C
I <sub>DSS</sub> Zero	Zana Cata Maltana Duain Courset	V <sub>DS</sub> = -250 V, V <sub>GS</sub> = 0 V			-1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -200 V, T <sub>C</sub> = 125°C			-10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.0 A		0.48	0.62	Ω
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = -40 \text{ V}, I_{D} = -3.0 \text{ A}$		4.8	-	S
	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$		910	1180	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		170	220	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			27	35	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = -125 V, I <sub>D</sub> = -9.4 A,		20	50	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		150	310	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	- 1.6 - 1 - 1		45	100	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		65	140	ns
Qg	Total Gate Charge	V <sub>DS</sub> = -200 V, I <sub>D</sub> = -9.4 A,		29	38	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -10 V	/	7.6		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	/	14	-	nC
						/
Drain-S	Source Diode Characteristics at	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-6.0	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				-24	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -6.0 A			-5.0	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -9.4 A,		190	-	ns
Q <sub>rr</sub>	-					

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 28.9 mH, I  $_{AS}$  = -6.0 A, V $_{DD}$  = -50 V, R $_{G}$  = 25  $\Omega$ , starting T $_{J}$  = 25°C. 3. I $_{SD}$  ≤ -9.4 A, di/dt ≤ 300 A/ $\mu$ s , V $_{DD}$  ≤ BV $_{DSS}$ , starting T $_{J}$  = 25°C. 4. Essentially independent of operating temperature.

# **Typical Characteristics**

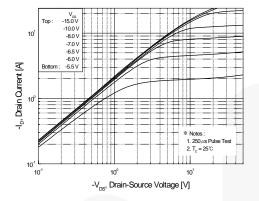


Figure 1. On-Region Characteristics

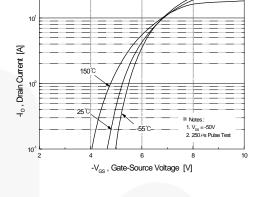


Figure 2. Transfer Characteristics

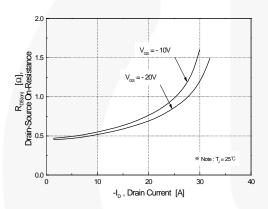


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

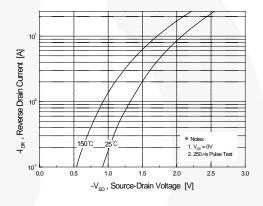


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

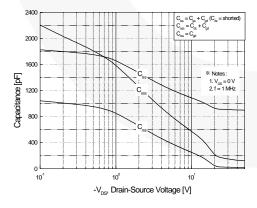


Figure 5. Capacitance Characteristics

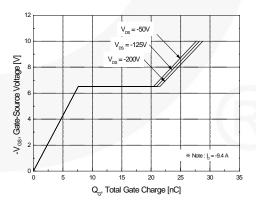


Figure 6. Gate Charge Characteristics

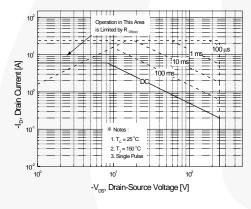
# 1.2 (Control Source Brown Voltage Brown Volt

Typical Characteristics (Continued)

2.5 (Declaration Temperature [°C]

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



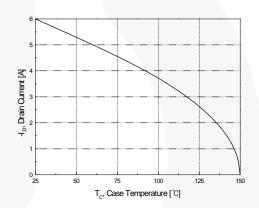


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

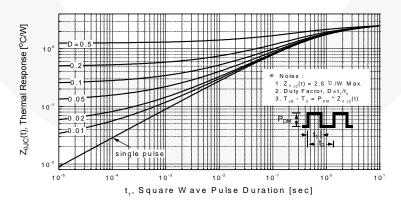


Figure 11. Transient Thermal Response Curve

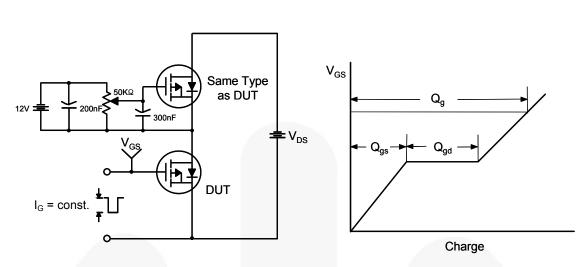


Figure 12. Gate Charge Test Circuit & Waveform

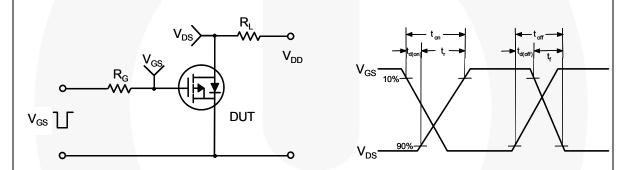


Figure 13. Resistive Switching Test Circuit & Waveforms

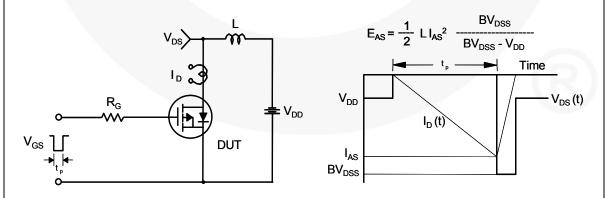
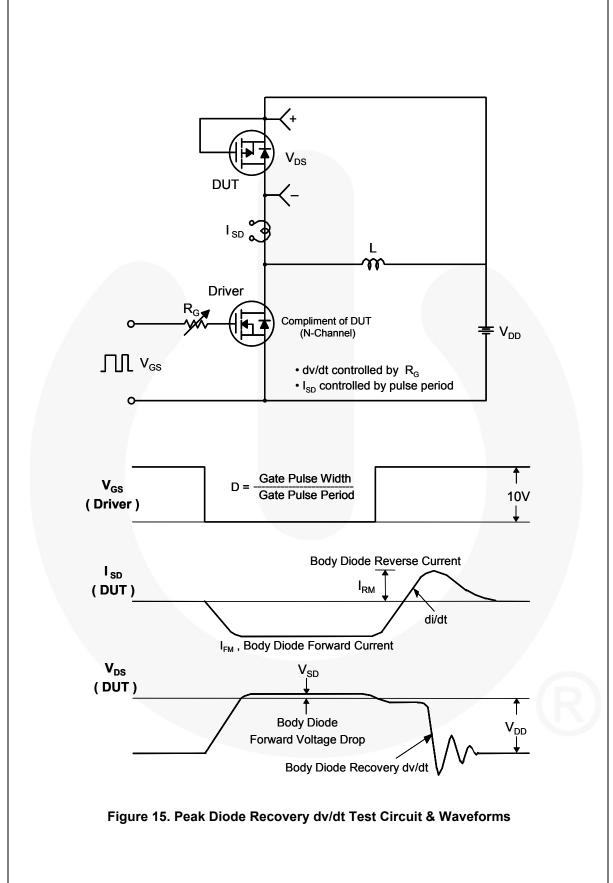


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



# **Mechanical Dimensions**

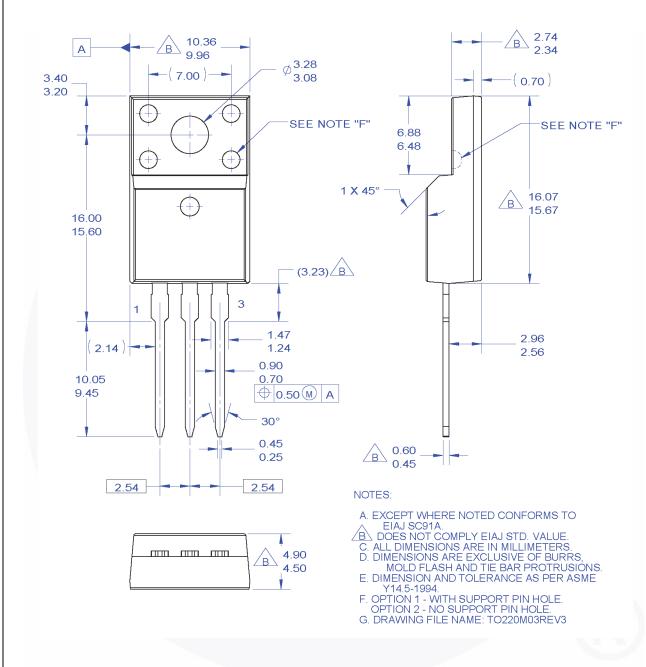


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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